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L43 and "foot"	14

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Search:

L46

Search History

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DB=PGPB; PLUR=YES; OP=OR

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<u>L45</u>	L44 same "external"	1	<u>L45</u>
<u>L44</u>	L43 same (recess\$4 near7 lid)	11	<u>L44</u>
<u>L43</u>	l42 same lid	327	<u>L43</u>
<u>L42</u>	substrate near6 (die or chip)	22887	<u>L42</u>

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<u>L41</u>	L39 same (recess\$4 near7 lid)	22	<u>L41</u>
<u>L40</u>	L39 same lid	641	<u>L40</u>
<u>L39</u>	substrate near6 (die or chip)	36825	<u>L39</u>
<u>L38</u>	5949655	40	<u>L38</u>
<u>L37</u>	6352195	2	<u>L37</u>
<u>L36</u>	6617647	1	<u>L36</u>
<u>L35</u>	5899714	28	<u>L35</u>
<u>L34</u>	method near10 forming near10 ("deep well" or "deep-well")	23	<u>L34</u>

<u>L33</u>	methode near10 forming near10 ("deep well" or "deep-well")	0	<u>L33</u>
<u>L32</u>	methode near4 forming near5 ("deep well" or "deep-well")	0	<u>L32</u>
<u>L31</u>	(deep near4 well) same ion same method	142	<u>L31</u>
<u>L30</u>	L28 and "method of forming"	0	<u>L30</u>
<u>L29</u>	L28 and "method of making"	0	<u>L29</u>
<u>L28</u>	L26 same well	18657	<u>L28</u>
<u>L27</u>	L26 well	2205306	<u>L27</u>
<u>L26</u>	(deep nera4 well) same ion same method	20083	<u>L26</u>
<i>DB=PGPB; PLUR=YES; OP=OR</i>			
<u>L25</u>	L24 and "add or extent or increase"	0	<u>L25</u>
<u>L24</u>	L23 and "second depth"	7	<u>L24</u>
<u>L23</u>	L22 and "first depth"	8	<u>L23</u>
<u>L22</u>	L20 and (Implant\$5 near15 (deep near3 well))	239	<u>L22</u>
<u>L21</u>	L20 (Implant\$5 near15 (deep near3 well))	239	<u>L21</u>
<u>L20</u>	(Implant\$5 near15 (deep near3 well))	239	<u>L20</u>
<i>DB=JPAB; PLUR=YES; OP=OR</i>			
<u>L19</u>	L18 same (deposit\$5 near5 epitax\$5)	0	<u>L19</u>
<u>L18</u>	(Implant\$5 near15 (deep near3 well))	25	<u>L18</u>
<i>DB=EPAB; PLUR=YES; OP=OR</i>			
<u>L17</u>	L16 same (deposit\$5 near5 epitax\$5)	0	<u>L17</u>
<u>L16</u>	(Implant\$5 near15 (deep near3 well))	3	<u>L16</u>
<i>DB=USPT; PLUR=YES; OP=OR</i>			
<u>L15</u>	L14 same (deposit\$5 near5 epitax\$5)	5	<u>L15</u>
<u>L14</u>	(Implant\$5 near15 (deep near3 well))	433	<u>L14</u>
<u>L13</u>	L12 same (deposit\$5 near5 epitax\$5)	5	<u>L13</u>
<u>L12</u>	(Implant\$5 near5 (deep near3 well))	325	<u>L12</u>
<u>L11</u>	5248624	14	<u>L11</u>
<u>L10</u>	L9	28	<u>L10</u>
<u>L9</u>	5899714	28	<u>L9</u>
<u>L8</u>	6040598	1	<u>L8</u>
<i>DB=PGPB; PLUR=YES; OP=OR</i>			
<u>L7</u>	L6 and (wider near10 ("second gate" near5 "second part"))	0	<u>L7</u>
<u>L6</u>	L5 and ("first gate" and "second gate")	66	<u>L6</u>
<u>L5</u>	L4 and base and ("first gate" and "second gate")	66	<u>L5</u>
<u>L4</u>	"high-breakdown-voltage" OR "high breakdown voltage"	1369	<u>L4</u>
<i>DB=USPT; PLUR=YES; OP=OR</i>			
<u>L3</u>	L2 and (gate near8 (wider or narrower))	11	<u>L3</u>
<u>L2</u>	L1 and base and ("first gate" and "second gate")	157	<u>L2</u>
<u>L1</u>	"high-breakdown-voltage" OR "high breakdown voltage"	3531	<u>L1</u>

END OF SEARCH HISTORY